

ABSTRACT OF THE DISCLOSURE

This invention provides a method of manufacturing a thin-film semiconductor device by a smaller number of processes with reduced influence on a device formation layer at the time of separation. This manufacturing method includes the step of preparing a member having, on a separation layer, a semiconductor film having a semiconductor element and/or semiconductor integrated circuit, the step of forming kerfs from the semiconductor film side of the member, and the separation step of, after the kerf formation step, separating a desired region of the semiconductor element and/or semiconductor integrated circuit from the member.

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